

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	61472	ono	USPAT; EPO; JPO	2000/11/17 16:23
2	L5	34	(reoxidized or re-oxidized) near5 nitride	USPAT; EPO; JPO	2000/11/17 16:24
3	L9	0	5 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 16:30
4	L13	5	5 and steam	USPAT; EPO; JPO	2000/11/17 16:30
5	L25	804	1 with gate	USPAT; EPO; JPO	2000/11/17 16:29
6	L29	34	25 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
7	L33	29	25 and water	USPAT; EPO; JPO	2000/11/17 18:06
8	L37	55	25 and steam	USPAT; EPO; JPO	2000/11/17 18:06
9	L41	3	25 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
10	L21	3	5 and water	USPAT; EPO; JPO	2000/11/17 16:32
11	L45	102	29 33 37 41	USPAT; EPO; JPO	2000/11/17 16:40
12	L49	5	45 and (RTN or nitridation)	USPAT; EPO; JPO	2000/11/17 17:47
13	L53	37	45 and ((heat\$3 or anneal\$3) near10 (nitrous oxide))	USPAT; EPO; JPO	2000/11/17 16:58
14	L57	1	45 and ((heat\$3 or anneal\$3) near10 (nitrous adj oxide))	USPAT; EPO; JPO	2000/11/17 16:59
15	L61	6	45 and ((heat\$3 or anneal\$3) near10 ("N.sub.2" adj O))	USPAT; EPO; JPO	2000/11/17 16:59
16	L65	1183	1 and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 17:51
17	L69	7976	(stabiliz\$3 or crystalliz\$3 or crystaliz\$3) near5 (oxide or dielectric)	USPAT; EPO; JPO	2000/11/17 17:54
18	L77	836	69 and steam	USPAT; EPO; JPO	2000/11/17 17:55
19	L81	1	69 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 17:55

	L #	Hits	Search Text	DBs	Time Stamp
20	L73	25	69 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 17:56
21	L85	95	1 and (wet adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
22	L89	8368	1 and water	USPAT; EPO; JPO	2000/11/17 18:08
23	L93	952	1 and steam	USPAT; EPO; JPO	2000/11/17 18:06
24	L97	7	1 and (pyrogenic adj (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:06
25	L101	681	(85 89 93 97) and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 18:09
26	L105	409	1 and (water near10 (oxide or oxidation))	USPAT; EPO; JPO	2000/11/17 18:09
27	L109	202	(85 105 93 97) and (time near3 temperature)	USPAT; EPO; JPO	2000/11/17 18:10

wet <near/5> oxidation <and> (rapid <or> RT[x])

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